

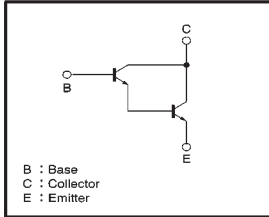
# Medium Power Transistor (60V, 1A)

## 2SD1834

### ●Features

- 1) Darlington connection for high DC current gain.  
(typically, DC current gain=15000 at  $V_{CE}=3V$ ,  $I_C=0.5A$ )
- 2) High input impedance.

### ●Circuit diagram



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	$V_{CES}$	60	V *2
Emitter-base voltage	$V_{EBO}$	7	V
Collector current	$I_C$	1	A (DC)
		2	A (Pulse) *1
Collector power dissipation	$P_C$	0.5	W
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{stg}$	-55~+150	°C

\*1 Single pulse  $P_w=100ms$   
\*2  $R_{\theta E}=0\Omega$

### ●Packaging specifications and hFE

Type	2SD1834
Package	MPT3
hFE	2k~
Marking	DE*
Code	T100
Basic ordering unit (pieces)	1000

\* Denotes hFE

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	60	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	$BV_{CEO}$	60	—	—	V	$I_C=100\mu A$ , $R_{\theta E}=0\Omega$
Emitter-base breakdown voltage	$BV_{EBO}$	7	—	—	V	$I_E=50\mu A$
Collector cutoff current	$I_{CBO}$	—	—	1	$\mu A$	$V_{CB}=60V$
Emitter cutoff current	$I_{EBO}$	—	—	1	$\mu A$	$V_{EB}=6V$
DC current transfer ratio	hFE	2000	—	—	—	$V_{CE}/I_C=3V/500mA$ *
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	0.9	1.5	V	$I_C/I_E=500mA/500\mu A$
Output capacitance	$C_{ob}$	—	7	—	pF	$V_{CB}=10V$ , $I_E=0A$ , $f=1MHz$

\* Measured using pulse current.

(94S-340-D64)

# Muting Transistor (15V, 1A)

## 2SD1468S / 2SD1865

### ●Features

- 1) Low saturation voltage, typically  $V_{CE(sat)}=0.006V$  at  $I_C/I_E=1mA/0.1mA$ .
- 2) Ideal for low voltage, high current drives.
- 3) High DC current gain and high current.

### ●Packaging specifications and hFE

Type	2SD1468S	2SD1865
Package	SPT	ATV
hFE	QRS	QR
Code	TP	TV2
Basic ordering unit (pieces)	5000	2500

### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	30	V
Collector-emitter voltage	$V_{CEO}$	15	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	1	A
Collector power dissipation	2SD1468S	0.3	W
	2SD1865	0.6	
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{stg}$	-55~+150	°C

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	30	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	$BV_{CEO}$	15	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	$BV_{EBO}$	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB}=20V$
Emitter cutoff current	$I_{EBO}$	—	—	0.5	$\mu A$	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	0.08	0.4	V	$I_C/I_E=0.5A/50mA$
DC current transfer ratio	2SD1468S	hFE	120	—	560	$V_{CE}/I_C=3V/0.1A$
	2SD1865	—	120	—	390	
Transition frequency	$f_T$	50	150	—	MHz	$V_{CE}=5V$ , $I_E=-50mA$ , $f=100MHz$
Output capacitance	$C_{ob}$	—	15	30	pF	$V_{CB}=10V$ , $I_E=0A$ , $f=1MHz$

(94L-767-D65)

### Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the product described in this document are for reference only. Upon actual use, therefore, please request that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or otherwise dispose of the same, no express or implied right or license to practice or commercially exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document use silicon as a basic material.  
Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

#### About Export Control Order in Japan

Products described herein are the objects of controlled goods in Annex 1 (Item 16) of Export Trade Control Order in Japan.

In case of export from Japan, please confirm if it applies to "objective" criteria or an "informed" (by MITI clause) on the basis of "catch all controls for Non-Proliferation of Weapons of Mass Destruction.